

DESCRIPTION

The MXT0515 uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

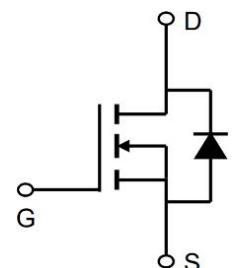
GENERAL FEATURES

- $V_{DS}=150V$, $I_D=220A$
- $R_{DS(ON)}(\text{Typ.})=5.0m\Omega$ @ $V_{GS}=6V$
- $R_{DS(ON)}(\text{Typ.})=4.5m\Omega$ @ $V_{GS}=10V$
- Surface-mounted package
- Advanced trench cell design

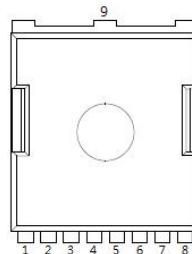
APPLICATION

- Power Tool appliances
- High Power inverter system
- BMS appliances

PINOUT



Schematic diagram



Top View TOLL-8L

Pin	Description
1	Gate(G)
2,3,4,5,6,7,8	Source(S)
9	Drain(D)

ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MXT0515	-55°C to 175°C	TOLL-8L	2000

ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 25	V
Drain Current-Continuous($V_{GS}=10V$, $T_c=25^\circ C$) ^(Note1)	I_D	220	A
Drain Current-Continuous($V_{GS}=10V$, $T_c=100^\circ C$) ^(Note1)	I_D	120	A
Pulsed Drain Current ^(Note1)	I_{DM}	680	A
Single Pulse Avalanche Energy	E_{AS}	1250	mJ
Continuous-Source Current	I_S	220	A
Avalanche Current	I_{AS}	160	A
Drain Power Dissipation	P_{tot}	375	W
Operating Junction and Storage Temperature Range	T_J , T_{STG}	-55 to 175	°C
Thermal Resistance, Junction-to-Ambient ^(Note2)	$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction-to-Case ^(Note2)	$R_{\theta JC}$	0.4	°C/W

Note 1. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Note 2. Surface Mounted on minimum footprint pad area.


ELECTRICAL CHARACTERISTICS($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
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Off Characteristics

Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	150	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=120\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 25\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA

On Characteristics

Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2	-	4	V
Drain-Source On-State Resistance ^(Note1)	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=6\text{V}, I_{\text{D}}=25\text{A}$	-	5.0	6.0	$\text{m}\Omega$
		$V_{\text{GS}}=10\text{V}, I_{\text{D}}=50\text{A}$	-	4.5	5.0	$\text{m}\Omega$

Dynamic Characteristics^(Note2)

Input Capacitance	C_{iss}	$V_{\text{DS}}=75\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	9320	-	pF
Output Capacitance	C_{oss}		-	570	-	pF
Reverse Transfer Capacitance	C_{rss}		-	60	-	pF

Switching Characteristics^(Note2)

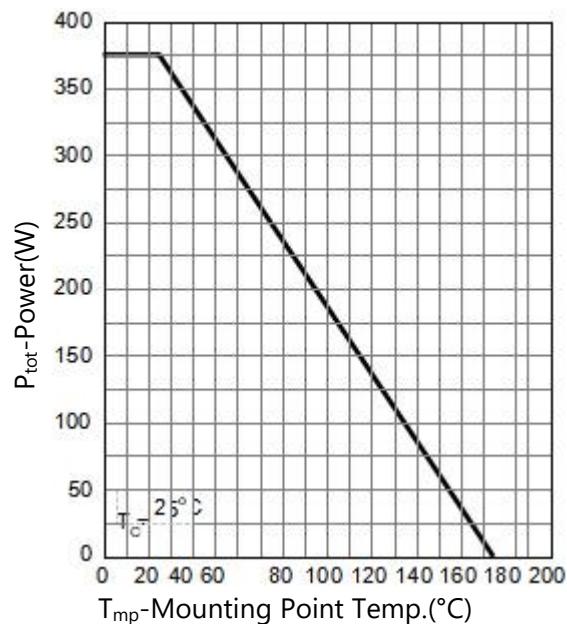
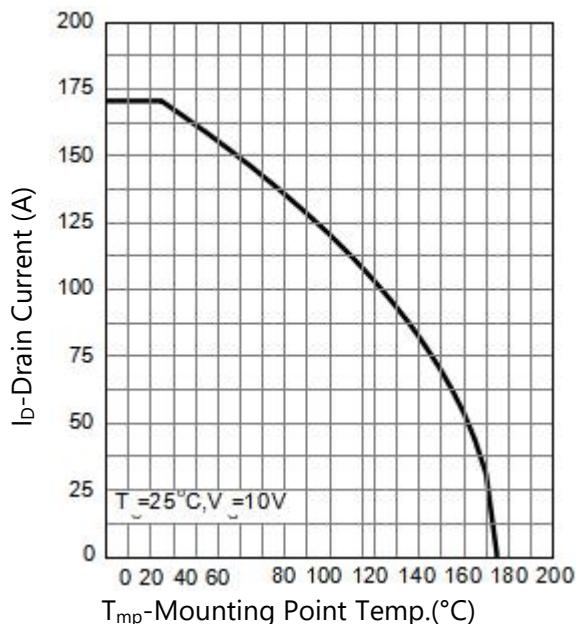
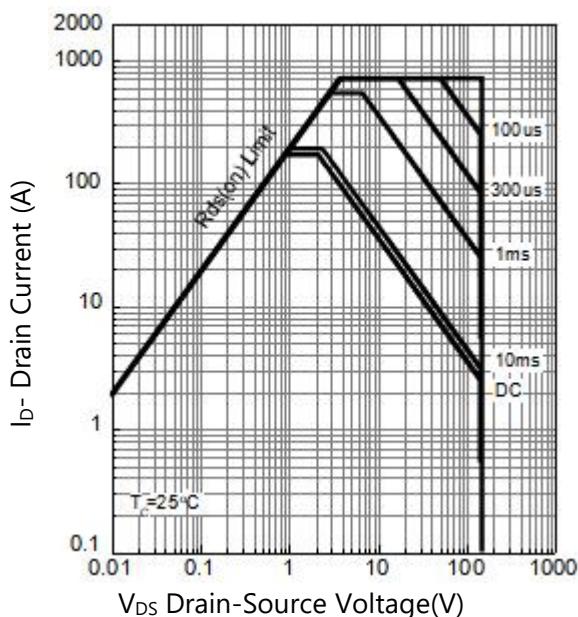
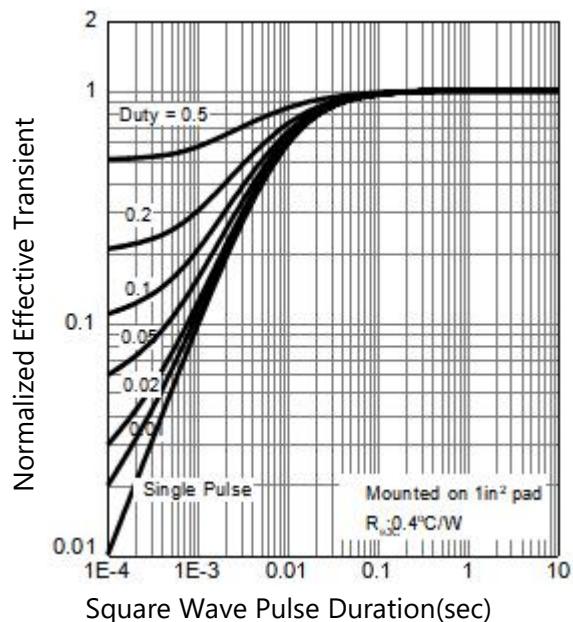
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DS}}=75\text{V}, I_{\text{DS}}=50\text{A}, V_{\text{GEN}}=10\text{V}, R_{\text{G}}=3.9\Omega, R_{\text{L}}=1.5\Omega,$	-	24	-	nS
Turn-on Rise Time	t_{r}		-	70	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	112	-	nS
Turn-Off Fall Time	t_{f}		-	75	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=75\text{V}, I_{\text{DS}}=50\text{A}, V_{\text{GS}}=10\text{V}$	-	158	-	nC
Gate-Source Charge	Q_{gs}		-	48	-	nC
Gate-Drain Charge	Q_{gd}		-	39	-	nC

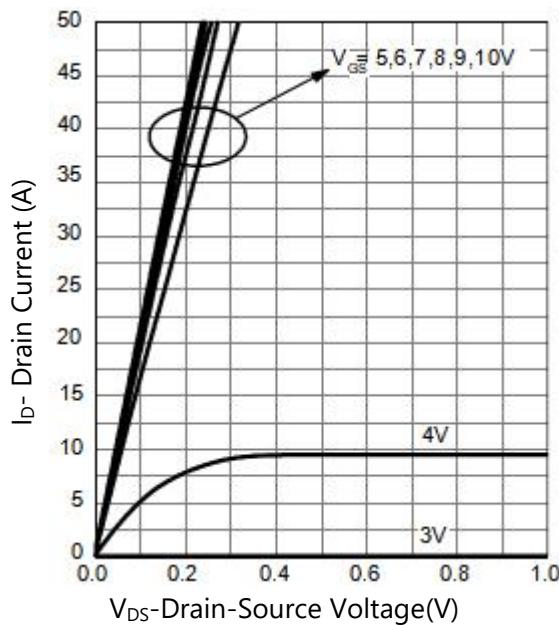
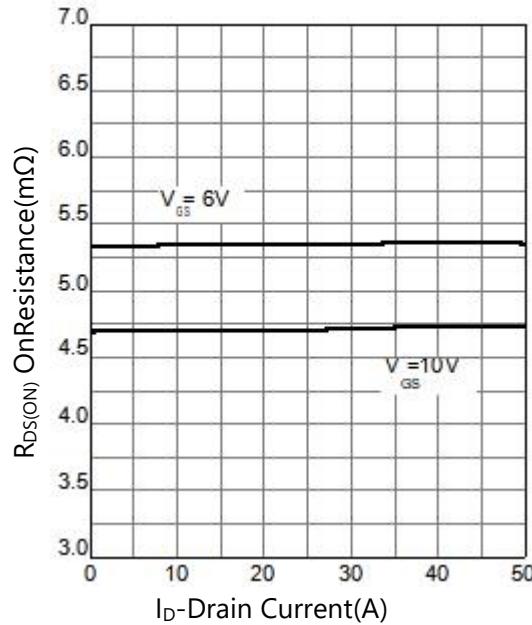
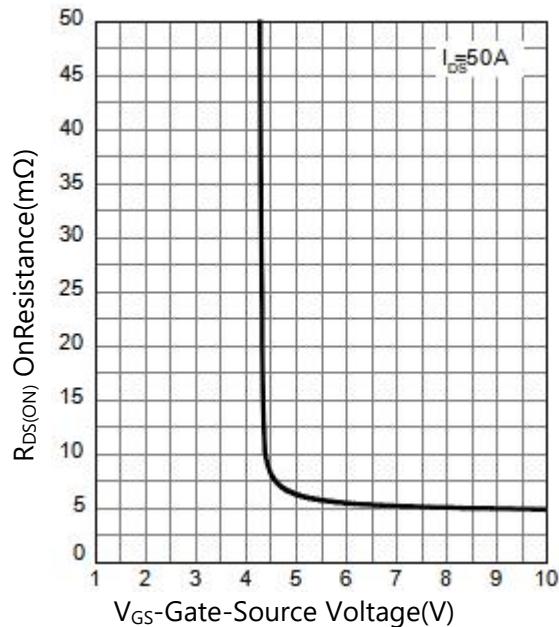
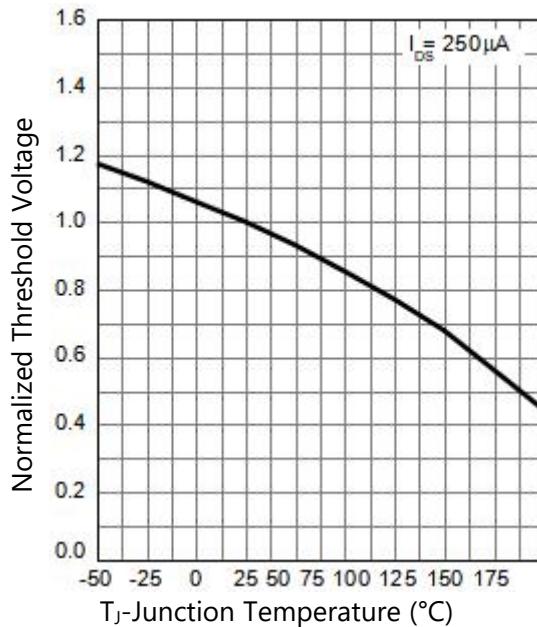
Drain-Source Diode Characteristics

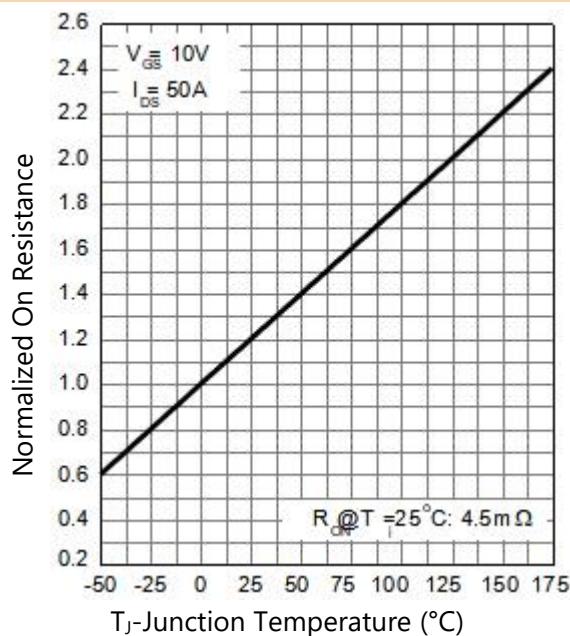
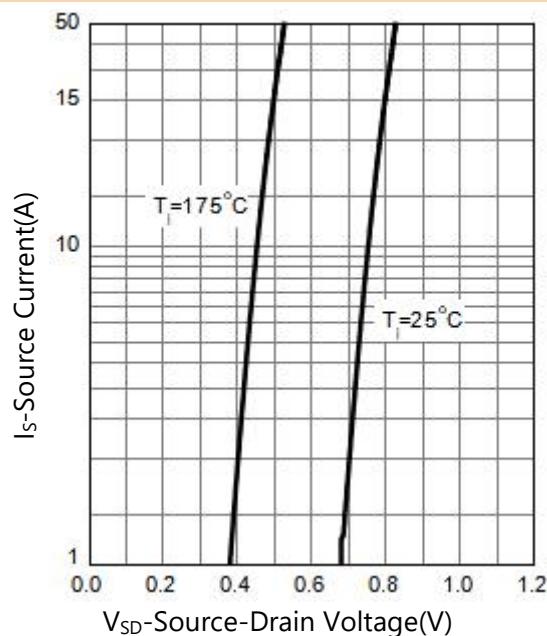
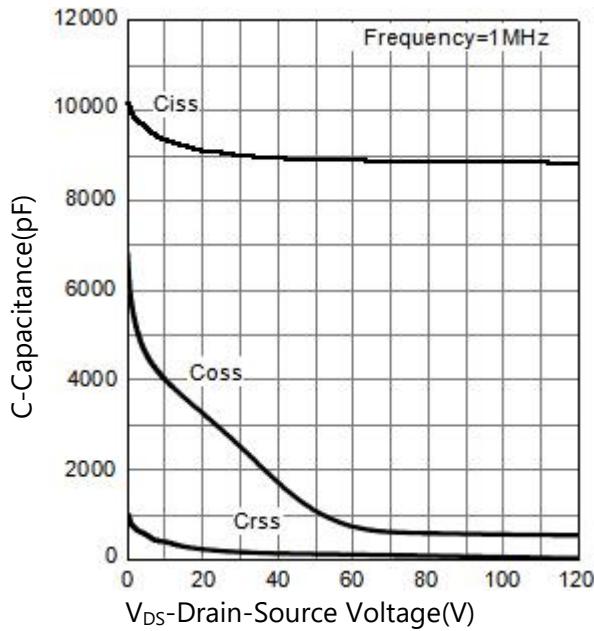
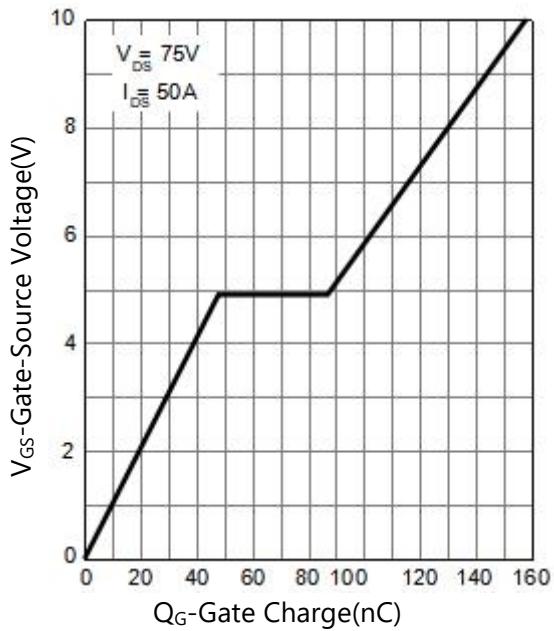
Diode Forward Voltage ^(Note1)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{SD}}=50\text{A}$	-	-	1.3	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}}=0\text{V}, I_{\text{DS}}=50\text{A}, \frac{di}{dt}=100\text{A}/\mu\text{s}$	-	115	-	nS
Reverse Recovery Charge	Q_{rr}		-	480	-	nC

Note 1. The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

Note 2. Guaranteed by design, not subject to production testing

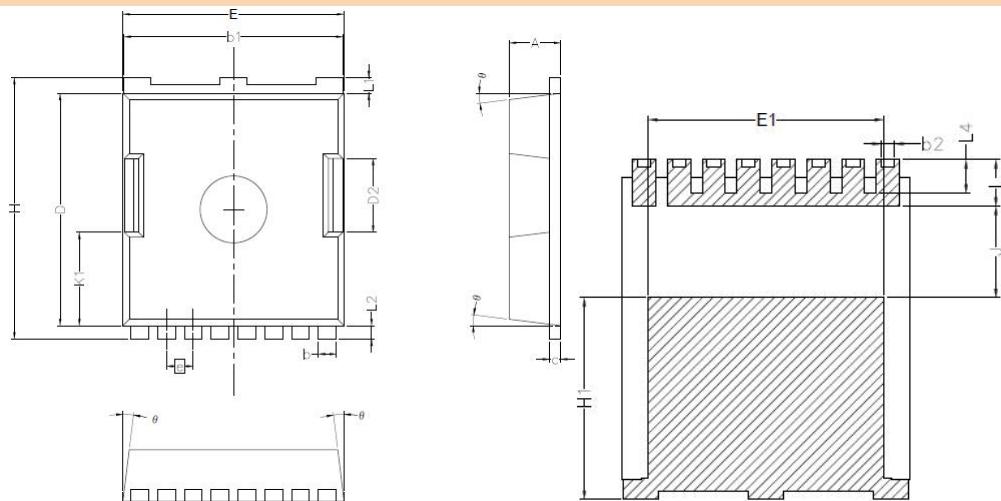

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 1. Power Capability

Figure 2. Current Capability

Figure 3. Safe Operation Area

Figure 4. Transient Thermal Impedance



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 5. Output Characteristics

Figure 6. On Resistance

Figure 7. Transfer Characteristics

Figure 8. Normalized Threshold Voltage



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 9. Normalized On Resistance

Figure 10. Diode Forward Current

Figure 11. Capacitance

Figure 12. Gate Charge


PACKAGE INFORMATION

TOLL-8L



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	2.20	2.40
b	0.90	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°